

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Hongyong ZHANG et al.

Serial No. 09/633,869

Filed: August 7, 2000

For: METHOD FOR LASER-PROCESSING
SEMICONDUCTOR DEVICE



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Group Art Unit: 2812

Examiner: Victor Simkovic

Date: October 5, 2001

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AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action dated July 5, 2001 please amend the above identified application as follows.

IN THE CLAIMS:

Please add new claims 37-72 as follows:

~~--37. A method for fabricating a semiconductor device having at least one thin film transistor comprising a channel region and a gate electrode, comprising the steps of:~~
forming a semiconductor film comprising amorphous silicon over a substrate; and
irradiating said semiconductor film with a laser light having an elongated irradiation area while relatively moving said laser light along a scan direction,
wherein said scanning direction is parallel to said channel region.

38. The method of claim 37, wherein said laser light is irradiated from an upper side of said gate electrode.

39. The method of claim 37, further comprising a step of heating said semiconductor film.

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01 FC:102 NVA199528.1
02 FC:103

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